









ADC128S102-SEP SNAS825A - DECEMBER 2021 - REVISED APRIL 2022

ADC128S102-SEP Radiation-Tolerant, 8-Channel, 50-kSPS to 1-MSPS, 12-Bit ADC

1 Features

- Radiation tolerant:
 - Single-event latch-up (SEL) immune up to LET = 43 MeV-cm²/mg at 125°C
 - Single-event functional interrupt (SEFI) characterized up to LET = 43 MeV-cm²/mg
 - Total ionizing dose (TID) RLAT/RHA characterized up to 30 krad(Si)
- Space-enhanced plastic (space EP):
 - Meets ASTM E595 outgassing specification
 - Vendor item drawing (VID) V62/22608
 - Military temperature range: –55°C to 125°C
 - One fabrication, assembly, and test site
 - Gold bond wire, NiPdAu lead finish
 - Wafer lot traceability
 - Extended product life cycle
 - Extended product change notification
- Wide supply range:
 - V_A: 2.7 V to 5.25 V
 - V_D: 2.7 V to V_A
- SPI™-, QSPI™-, MICROWIRE®-, DSP-compatible
- Conversion rate: 50 kSPS to 1 MSPS
- DNL: +1.8 LSB to -0.99 LSB (maximum)
- INL: +1.6 to -1.6 LSB (maximum)
- Power consumption:
 - 3-V supply: 2.7 mW (typical)
 - 5-V supply: 11 mW (typical)

2 Applications

- Satellite electrical power system (EPS)
- Command and data handling (C&DH)
- Optical imaging payload
- Voltage, current, and temperature monitoring
- Accelerators

3 Description

The ADC128S102-SEP is a low-power, eight-channel, CMOS, 12-bit analog-to-digital converter (ADC) specified for conversion throughput rates of 50 kSPS to 1 MSPS. The converter is based on a successiveapproximation register (SAR) architecture with an internal track-and-hold circuit. The device can be configured to accept up to eight input signals at inputs IN0 through IN7.

The output serial data is straight binary and compatible with several standards, such as SPI, QSPI, MICROWIRE, and many common DSP serial interfaces.

The ADC128S102-SEP can be operated with independent analog and digital supplies. The analog supply (VA) can range from 2.7 V to 5.25 V, and the digital supply (V_D) can range from 2.7 V to V_A. Normal power consumption using a 3-V or 5-V supply is 2.3 mW and 10.7 mW, respectively. The power-down feature reduces the power consumption to 16.5 μW using a 3-V supply and 30 µW using a 5-V supply.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
ADC128S102-SEP	TSSOP (16)	5.00 mm × 4.40 mm		

For all available packages, see the orderable addendum at the end of the data sheet.

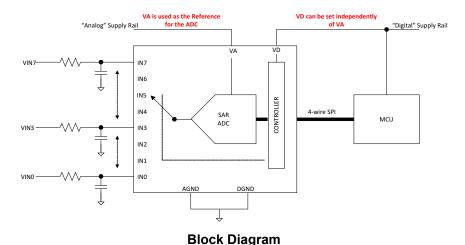




Table of Contents

1 Features1	7.5 Programming	. 18
2 Applications1	8 Application and Implementation	
3 Description1	8.1 Application Information	. 20
4 Revision History2	8.2 Typical Application	
5 Pin Configuration and Functions3	9 Power Supply Recommendations	
6 Specifications4	9.1 Power-Supply Sequence	
6.1 Absolute Maximum Ratings4	9.2 Power Management	
6.2 ESD Ratings	9.3 Power-Supply Noise Considerations	
6.3 Recommended Operating Conditions4	10 Layout	
6.4 Thermal Information5	10.1 Layout Guidelines	
6.5 Electrical Characteristics6	10.2 Layout Example	
6.6 Timing Requirements8	11 Device and Documentation Support	
6.7 Switching Characteristics8	11.1 Receiving Notification of Documentation Updates	24
6.8 Timing Diagrams9	11.2 Support Resources	. 24
6.9 Typical Characteristics10	11.3 Trademarks	
7 Detailed Description15	11.4 Electrostatic Discharge Caution	24
7.1 Overview	11.5 Glossary	24
7.2 Functional Block Diagram15	12 Mechanical, Packaging, and Orderable	
7.3 Feature Description15	Information	<mark>2</mark> 4
7.4 Device Functional Modes17	12.1 Engineering Samples	24

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision * (December 2021) to Revision A (April 2022)Page• Changed document status from advance information to production data1

5 Pin Configuration and Functions

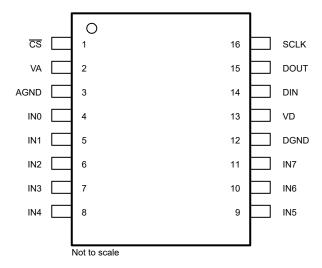


Figure 5-1. PW Package, 16-Pin TSSOP (Top View)

Table 5-1. Pin Functions

	PIN	TYPE	DECORPTION
NO.	NAME	ITPE	DESCRIPTION
1	CS	IN	Chip select. On the falling edge of $\overline{\text{CS}}$, a conversion process begins. Conversions continue as long as $\overline{\text{CS}}$ is held low.
2	V _A	Supply	Positive analog supply pin. This voltage is also used as the reference voltage. Connect this pin to a quiet 2.7-V to 5.25-V source and bypass this pin to GND with 1-µF and 0.1-µF monolithic ceramic capacitors located within 1 cm of the power pin.
3	AGND	Supply	The ground return for the analog supply and signals.
4	IN0	IN	Analog input. This signal can range from 0 V to V _{REF} .
5	IN1	IN	Analog input. This signal can range from 0 V to V _{REF} .
6	IN2	IN	Analog input. This signal can range from 0 V to V _{REF} .
7	IN3	IN	Analog input. This signal can range from 0 V to V _{REF} .
8	IN4	IN	Analog input. This signal can range from 0 V to V _{REF} .
9	IN5	IN	Analog input. This signal can range from 0 V to V _{REF} .
10	IN6	IN	Analog input. This signal can range from 0 V to V _{REF} .
11	IN7	IN	Analog input. This signals can range from 0 V to V _{REF} .
12	DGND	Supply	The ground return for the digital supply and signals.
13	V _D	Supply	Positive digital supply pin. Connect this pin to a 2.7-V to V _A supply, and bypass this pin to GND with a 0.1-µF monolithic ceramic capacitor located within 1 cm of the power pin.
14	DIN	IN	Digital data input. The control register is loaded through this pin on rising edges of the SCLK pin.
15	DOUT	OUT	Digital data output. The output samples are clocked out of this pin on the falling edges of the SCLK pin.
16	SCLK	IN	Digital clock input. The specified performance range of frequencies for this input is 0.8 MHz to 16 MHz. This clock directly controls the conversion and readout processes.



6 Specifications

6.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted)(1)

	MIN	MAX	UNIT
Analog supply voltage (V _A)	-0.3	6.5	V
Digital supply voltage (V _D) ⁽²⁾	-0.3	V _A + 0.3	V
Voltage on analog input pins to AGND ⁽²⁾	AGND - 0.3	V _A + 0.3	V
Voltage on digital input and digital output pins to DGND ⁽²⁾	DGND - 0.3	V _D + 0.3	V
DGND to AGND	-0.3	0.3	V
Input current at any pin	-10	10	mA
Package input current	-20	20	mA
Power-dissipation at T _A = 25°C		See ⁽³⁾	
Junction temperature, T _J		150	°C
Storage temperature, T _{stg}	-65	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The maximum voltage is not to exceed 6.5 V
- (3) The absolute maximum junction temperature (T_Jmax) for this device is 150°C. The maximum allowable power dissipation is dictated by TJmax, the junction-to-ambient thermal resistance (θ_{JA}), and the ambient temperature (T_A), and can be calculated using the formula P_DMAX = (T_Jmax T_A)/θ_{JA}. The values for maximum power dissipation listed above will be reached only when the device is operated in a severe fault condition (e.g. when input or output pins are driven beyond the power supply voltages, or the power supply polarity is reversed). Such conditions should always be avoided.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatio discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001, all pins ⁽¹⁾	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾		

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	NOM	MAX	UNIT
V _A	Analog power supply	V _A to AGND	2.7		5.25	V
V_D	Digital power supply	V _D to DGND	2.7		V _A	V
V _{IN}	Digital input voltage		0		V _A	V
FSR	Full-scale analog input range		0		V _A	V
	Clock frequency		0.8		16	MHz
T _A	Ambient temperature		– 55	25	125	°C

Submit Document Feedback



6.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	ADC128S102-SEP PW (TSSOP) 16 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	110	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	42	°C/W
R _{0JB}	Junction-to-board thermal resistance	56	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	5	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	55	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



6.5 Electrical Characteristics

at AGND = DGND = 0 V, f_{SCLK} = 0.8 MHz to 16 MHz, f_{SAMPLE} = 50 kSPS to 1 MSPS, and C_L = 50 pF (unless otherwise noted); minimum and maximum values at T_A = -55°C to +125°C; typical values at T_A = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
ANALOG	SINPUTS						
DCL	Input leakage current		-1		1	μΑ	
S _{IN}	Input capacitance ⁽¹⁾	Track mode		33		pF	
ZIN	input capacitance.	Hold mode		3		Рι	
C PERF	FORMANCE						
	Resolution	No missing codes		12		Bits	
		V _A = V _D = 3 V		0.5	1.8		
ONL	Differential nonlinearity	VA - VD - 3 V	-0.99	-0.3		LSB	
)INL	Differential Horilinearity	V _A = V _D = 5 V		0.9	1.7	LOD	
		VA - VD - 5 V	-0.99	-0.5			
NII.	late and a colin colin	$V_A = V_D = 3 V$	-1.6	±0.6	1.6	1.00	
NL	Integral nonlinearity	$V_A = V_D = 5 V$	-1.5	±0.9	1.5	LSB	
		$V_A = V_D = 3 V$	-2.3	0.8	2.3		
OFF	Input offset error	$V_A = V_D = 5 V$	-2.3	1.1	2.3	LSB	
		$V_A = V_D = 3 V$	-1.5	±0.1	1.5		
DEM	Offset error match	$V_A = V_D = 5 V$	-1.5	±0.3	1.5	LSE	
	Full-scale error	V _A = V _D = 3 V	-2.1	0.8	2.1	LSB	
FSE		V _A = V _D = 5 V	-2.1	0.3	2.1		
	Full-scale error match	V _A = V _D = 3 V	-1.6	±0.1	1.6		
FSEM		$V_A = V_D = 5 V$	-1.6	±0.3	1.6	LSE	
AC PERF	FORMANCE	, , , , , , , , , , , , , , , , , , ,					
		$V_A = V_D = 3 V$		6.8			
PBW	Full-power bandwidth	V _A = V _D = 5 V		10		MHz	
	Signal-to-noise + distortion ratio	$V_A = V_D = 3 V$, $f_{IN} = 40.2 \text{ kHz}$, -0.02 dBFS	68	72			
SINAD		$V_A = V_D = 5 V$, $f_{IN} = 40.2 \text{ kHz}$, -0.02 dBFS	68	72		- dB	
		$V_A = V_D = 3 V$, $f_{IN} = 40.2 \text{ kHz}$, -0.02 dBFS	68.5	72			
SNR	Signal-to-noise ratio	$V_A = V_D = 5 V$, $f_{IN} = 40.2 \text{ kHz}$, -0.02 dBFS	68	72		dB	
TUD.	Takal la anno a ia diakanki an	$V_A = V_D = 3 V$, $f_{IN} = 40.2 \text{ kHz}$, -0.02 dBFS		-86	-72	٦D	
THD	Total harmonic distortion	$V_A = V_D = 5 V$, $f_{IN} = 40.2 \text{ kHz}$, -0.02 dBFS		-87	-72	dB	
) EDD	Country for the series	$V_A = V_D = 3 V$, $f_{IN} = 40.2 \text{ kHz}$, -0.02 dBFS	75	91		٩D	
SFDR	Spurious-free dynamic range	$V_A = V_D = 5 V$, $f_{IN} = 40.2 \text{ kHz}$, -0.02 dBFS	75	90		dB	
NOP	Effective number of hits	$V_A = V_D = 3 V$, $f_{IN} = 40.2 \text{ kHz}$, -0.02 dBFS	11.1	11.6		D:+-	
NOB	Effective number of bits	$V_A = V_D = 5 V$, $f_{IN} = 40.2 \text{ kHz}$, -0.02 dBFS	11	11.6		- Bits	
80	Channel to shore the letter	$V_A = V_D = 3 V$, $f_{IN} = 20 \text{ kHz}$, -0.02 dBFS		84		10	
SO	Channel-to-channel isolation	$V_A = V_D = 5 V$, $f_{IN} = 20 \text{ kHz}, -0.02 \text{ dBFS}$		85		dB	

Submit Document Feedback

Copyright © 2022 Texas Instruments Incorporated

6.5 Electrical Characteristics (continued)

at AGND = DGND = 0 V, f_{SCLK} = 0.8 MHz to 16 MHz, f_{SAMPLE} = 50 kSPS to 1 MSPS, and C_L = 50 pF (unless otherwise noted); minimum and maximum values at T_A = -55°C to +125°C; typical values at T_A = 25°C

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
	Intermodulation distortion,	$V_A = V_D = 3 V$, $f_{IN} = 19.5 \text{ kHz}$, -0.02 dBFS	-93	-77	
IMD	second order terms	$V_A = V_D = 5 \text{ V},$ $f_{IN} = 19.5 \text{ kHz}, -0.02 \text{ dBFS}$	-93	-77	15
טואוו	Intermodulation distortion,	$V_A = V_D = 3 V$, $f_{IN} = 19.5 \text{ kHz}, -0.02 \text{ dBFS}$	-91	-70	dB
	third order terms	$V_A = V_D = 5 \text{ V},$ $f_{IN} = 19.5 \text{ kHz}, -0.02 \text{ dBFS}$	-91	-70	
DIGITAL	INPUTS		·		
.,		V _A = V _D = 2.7 V to 3.6 V	2.1		.,
V _{IH}	Input high logic level	V _A = V _D = 4.75 V to 5.25 V	2.4		V
V _{IL}	Input low logic level	V _A = V _D = 2.7 V to 5.25 V		0.8	V
	Input current	V _{IN} = 0 V or V _D	±0.01	±2	μA
	Digital input capacitance ⁽¹⁾			3.5	pF
DIGITAL	OUTPUTS				
	Output format		Straight binary		
V _{OH}	Output high logic level	I _{SOURCE} = 200 μA, V _A = V _D = 2.7 V to 5.25 V	V _D - 0.5		V
V _{OL}	Output low logic level	I _{SOURCE} = 200 μA to 1 mA, V _A = V _D = 2.7 V to 5.25 V		0.4	V
	Hiigh-impedance output leakage current	V _A = V _D = 2.7 V to 5.25 V	±0.01	±1	μΑ
	Hiigh-impedance output capacitance ⁽¹⁾			3.5	pF
POWER	SUPPLY				
	Total supply current,	$V_A = V_D = 2.7 \text{ V to } 3.6 \text{ V}$ $f_{SAMPLE} = 1 \text{ MSPS}, f_{IN} = 40 \text{ kHz}$	0.9	1.5	
	normal mode (CS low)	$V_A = V_D = 4.75 \text{ V to } 5.25 \text{ V}$ $f_{SAMPLE} = 1 \text{ MSPS}, f_{IN} = 40 \text{ kHz}$	2.2	3.2	mA
I _A + I _D	Total supply current,	$V_A = V_D = 2.7 \text{ V to } 3.6 \text{ V}$ $f_{SAMPLE} = 0 \text{ kSPS}$	5.5	50	
	shutdown mode (CS high)	$V_A = V_D = 4.75 \text{ V to } 5.25 \text{ V}$ $f_{SAMPLE} = 0 \text{ kSPS}$	6	70	μA
	Power consumption,	$V_A = V_D = 3 V$ $f_{SAMPLE} = 1 MSPS$, $f_{IN} = 40 \text{ kHz}$	2.7	4.5	mW
P _C	normal mode (CS low)	$V_A = V_D = 5 V$ $f_{SAMPLE} = 1 MSPS$, $f_{IN} = 40 \text{ kHz}$	11	15.5	11177
' C	Power consumption,	$V_A = V_D = 3 V$ $f_{SAMPLE} = 0 kSPS$	16.5	150	μW
	shutdown mode (CS high)	$V_A = V_D = 5 V$ $f_{SAMPLE} = 0 kSPS$	30	350	μνν

⁽¹⁾ This parameter is specified by design and/or characterization and is not tested in production.



6.6 Timing Requirements

at $V_A = V_D = 2.7$ V to 5.25 V, AGND = DGND = 0 V, $f_{SCLK} = 0.8$ MHz to 16 MHz, $f_{SAMPLE} = 50$ kSPS to 1 MSPS, and $C_L = 50$ pF (unless otherwise noted); minimum and maximum values at $T_A = -55$ °C to +125°C; typical values at $T_A = 25$ °C.

			MIN	TYP	MAX	UNIT
CONVERS	SION CYCLE				'	
f _{SCLK}	Serial clock frequency	$V_A = V_D = 2.7 \text{ V to } 5.25 \text{ V}$	0.8		16	MHz
	Serial clock duty cycle	$V_A = V_D = 2.7 \text{ V to } 5.25 \text{ V}$	40%		60%	
f _S	Sample rate in continuous mode	$V_A = V_D = 2.7 \text{ V to } 5.25 \text{ V}$	50			kSPS
t _{CONVERT}	Conversion (hold) time	$V_A = V_D = 2.7 \text{ V to } 5.25 \text{ V}$			13	SCLK
t _{ACQ}	Acquisition (track) time	$V_A = V_D = 2.7 \text{ V to } 5.25 \text{ V}$			3	SCLK
t _{CYCLE}	Throughput time	$(t_{CONV} + t_{ACQ})$ at $V_A = V_D = 2.7 \text{ V to } 5.25 \text{ V}$			16	SCLK
SPI INTER	RFACE TIMINGS					
t _{CSH}	CS hold time after SCLK rising edg	е	10	2		ns
t _{CSS}	CS setup time prior to SCLK rising	edge	10	4.5		ns
t _{DS}	DIN setup time prior to SCLK rising	edge	10			ns
t _{DH}	DIN hold time after SCLK rising edge		10			ns
t _{CH}	SCLK high time		(0.4 x t _{SCLK}		ns
t _{CL}	SCLK low time		(0.4 x t _{SCLK}		ns

6.7 Switching Characteristics

at $V_A = V_D = 2.7$ V to 5.25 V, AGND = DGND = 0 V, $f_{SCLK} = 0.8$ MHz to 16 MHz, $f_{SAMPLE} = 50$ kSPS to 1 MSPS, and $C_L = 50$ pF (unless otherwise noted); minimum and maximum values at $T_A = -55^{\circ}\text{C}$ to +125°C; typical values at $T_A = 25^{\circ}\text{C}$.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
SPI INTERFACE TIMINGS									
t _{EN}	CS falling edge to DOUT enabled			5	30	ns			
t _{DACC}	DOUT access time after SCLK falling edge			17	27	ns			
t _{DHLD}	DOUT hold time after SCLK falling edge		7			ns			
	CS rising edge to DOUT high-impedance	DOUT falling		2.4	20	ns			
t _{DIS}	CS fishing edge to DOOT high-impedance	DOUT rising		0.9	20	ns			

Submit Document Feedback

Copyright © 2022 Texas Instruments Incorporated

6.8 Timing Diagrams

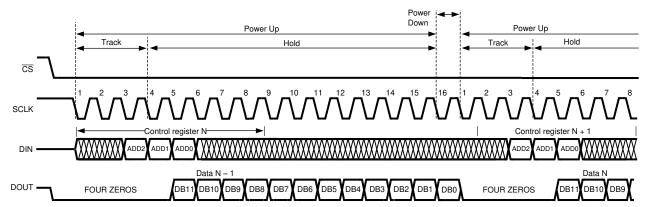


Figure 6-1. ADC128S102-SEP Operational Timing Diagram

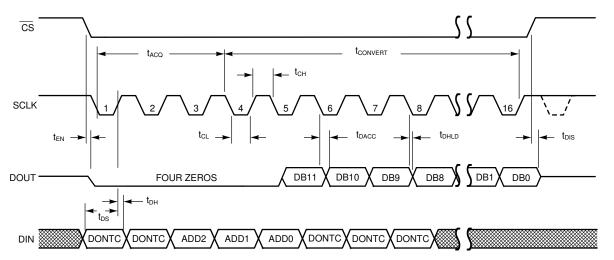


Figure 6-2. ADC128S102-SEP Serial Timing Diagram

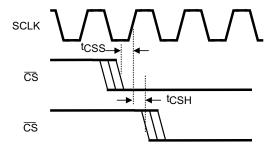
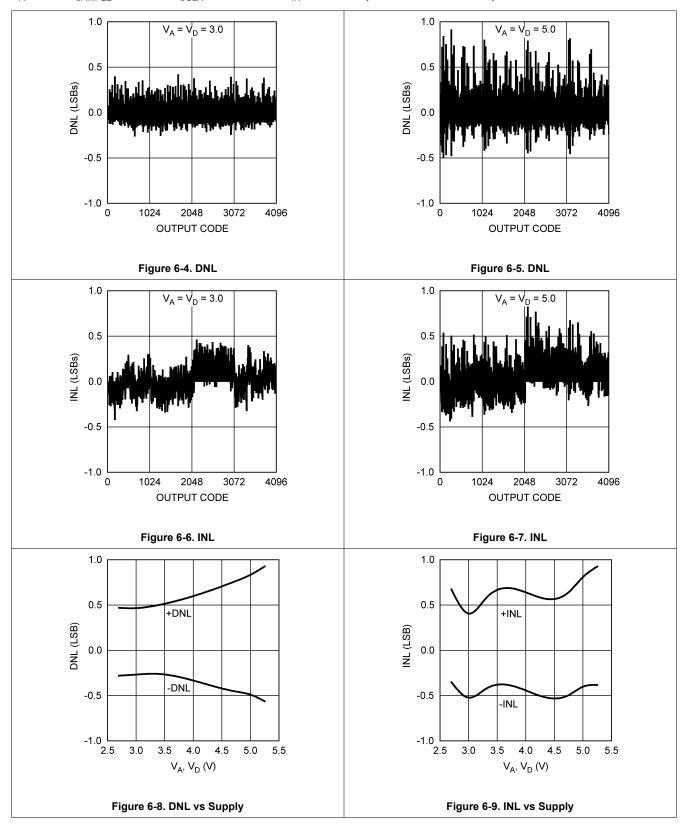


Figure 6-3. SCLK and $\overline{\text{CS}}$ Timing Parameters

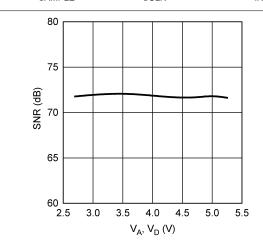


6.9 Typical Characteristics

 T_A = 25°C, f_{SAMPLE} = 1 MSPS, f_{SCLK} = 16 MHz, and f_{IN} = 40.2 kHz (unless otherwise noted)



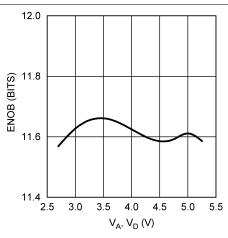
 T_A = 25°C, f_{SAMPLE} = 1 MSPS, f_{SCLK} = 16 MHz, and f_{IN} = 40.2 kHz (unless otherwise noted)



-70 -80 -90 2.5 3.0 3.5 4.0 4.5 5.0 5.5 V_A, V_D (V)

Figure 6-10. SNR vs Supply

Figure 6-11. THD vs Supply



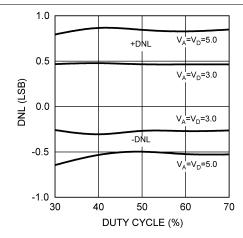
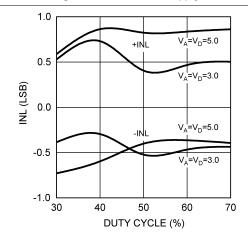


Figure 6-12. ENOB vs Supply

Figure 6-13. DNL vs SCLK Duty Cycle



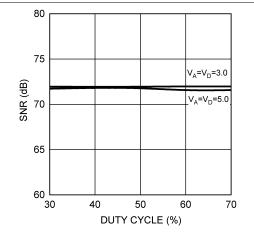
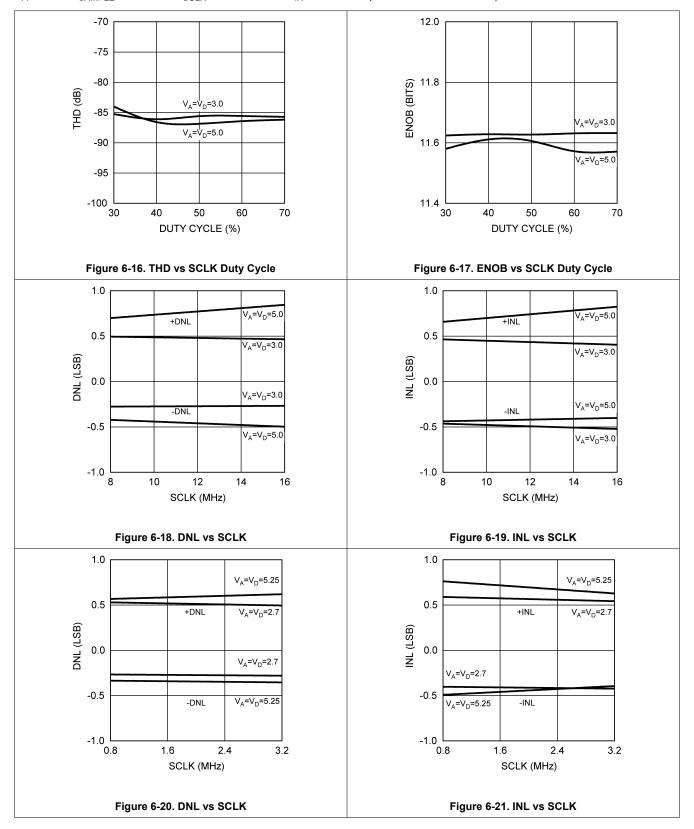


Figure 6-14. INL vs SCLK Duty Cycle

Figure 6-15. SNR vs SCLK Duty Cycle

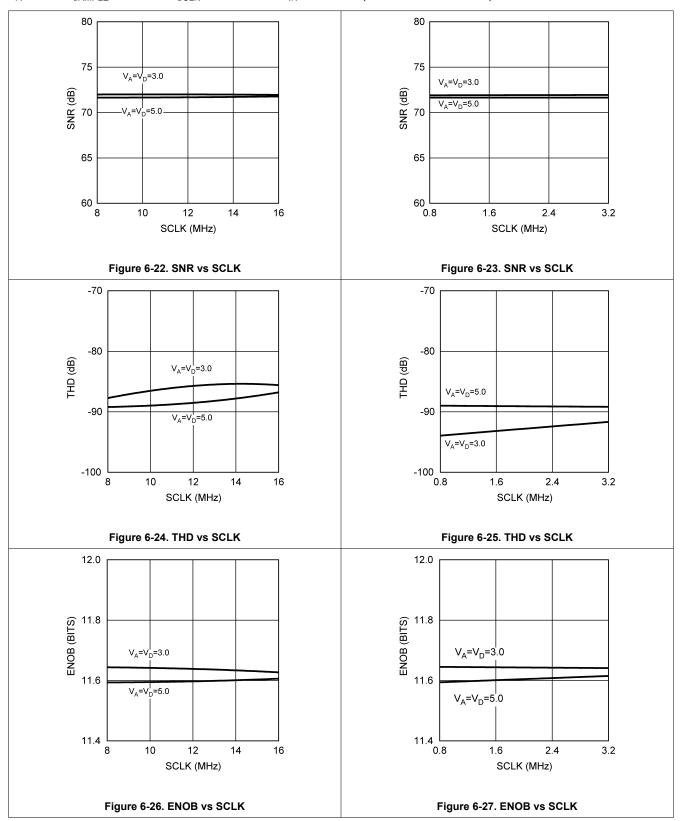


 T_A = 25°C, f_{SAMPLE} = 1 MSPS, f_{SCLK} = 16 MHz, and f_{IN} = 40.2 kHz (unless otherwise noted)



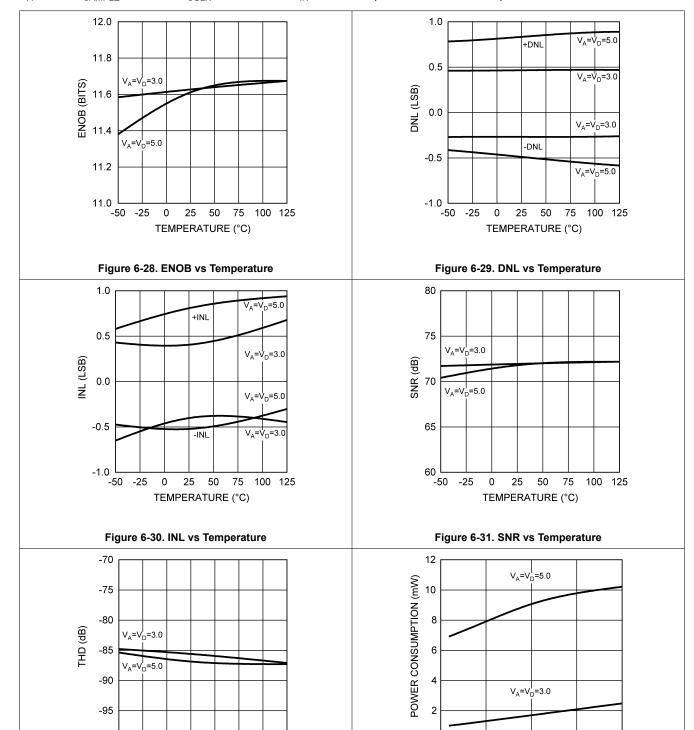


 T_A = 25°C, f_{SAMPLE} = 1 MSPS, f_{SCLK} = 16 MHz, and f_{IN} = 40.2 kHz (unless otherwise noted)





 T_A = 25°C, f_{SAMPLE} = 1 MSPS, f_{SCLK} = 16 MHz, and f_{IN} = 40.2 kHz (unless otherwise noted)



-100

-50

-25

0 25

50 75

TEMPERATURE (°C)

Figure 6-32. THD vs Temperature

100 125

12

16

0

0

4

8

SCLK (MHz)

Figure 6-33. Power Consumption vs SCLK

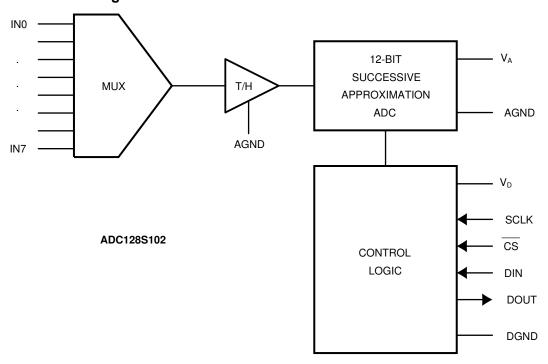
7 Detailed Description

7.1 Overview

The ADC128S102-SEP is a small, eight-channel, multiplexed, 12-bit, successive-approximation register analog-to-digital converter (SAR ADC) designed around a charge redistribution digital-to-analog converter (DAC). In addition to having 8 input channels, the ADC128S102-SEP can operate at sampling rates up to 1 MSPS.

The device provides an SPI-compatible serial interface.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 ADC128S102-SEP Transfer Function

The output format of the ADC128S102-SEP is straight binary. Code transitions occur midway between successive integer LSB values. The LSB width for the ADC128S102-SEP is V_A / 4096. Figure 7-1 illustrates the ideal transfer characteristic. The transition from an output code of 0000 0000 0000 to a code of 0000 0000 0001 is at 1/2 LSB, or a voltage of V_A / 8192. Other code transitions occur at steps of one LSB.

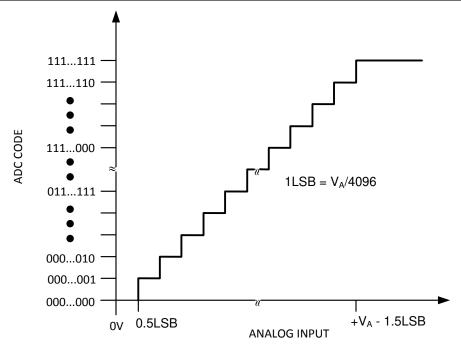


Figure 7-1. Ideal Transfer Characteristic

7.3.2 Analog Inputs

Figure 7-2 shows an equivalent circuit for one of the input channels of the ADC128S102-SEP. Diodes D1 and D2 provide ESD protection for the analog inputs. The operating range for the analog inputs is 0 V to V_A . Going beyond this range causes the ESD diodes to conduct and results in erratic operation.

Capacitor C1 in Figure 7-2 has a typical value of 3 pF and is mainly the package pin capacitance. Resistor R1 is the ON-resistance of the multiplexer and track-and-hold switch and is typically 500 Ω . Capacitor C2 is the ADC128S102-SEP sampling capacitor, and is typically 30 pF. The ADC128S102-SEP delivers best performance when driven by a low-impedance source (less than 100 Ω). This source is especially important when using the ADC128S102-SEP to sample dynamic signals. Also important when sampling dynamic signals is a band-pass or low-pass filter, which reduces harmonics and noise in the input. These filters are often referred to as antialiasing filters.

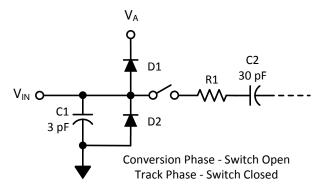


Figure 7-2. Equivalent Input Circuit

7.3.3 Digital Inputs and Outputs

The digital inputs of the ADC128S102-SEP (SCLK, $\overline{\text{CS}}$, and DIN) have an operating range of 0 V to V_A. The inputs are not prone to latch-up and can be asserted before the digital supply (V_D) without any risk. The digital output (DOUT) operating range is controlled by V_D. The output high voltage is V_D – 0.5 V (minimum) when the output low voltage is 0.4 V (maximum).

7.3.4 Radiation Environments

Careful consideration must be given to environmental conditions when using a product in a radiation environment.

7.3.4.1 Total lonizing Dose

Testing and qualification of these products is done on a wafer level according to *MIL-STD-883G*, *Test Method 1019.7*. Testing is done according to condition A and the extended room temperature anneal test described in section 3.11 for application environment dose rates less than 51.61 rad(Si)/s. Wafer level TID data are available with lot shipments.

7.3.4.2 Single Event Latch-Up

One-time single event latch-up (SEL) was preformed according to EIA/JEDEC Standard, EIA/JEDEC57. The linear energy transfer threshold (LET_{th}) shown in the *Features* section is the maximum LET tested. A test report is available upon request.

7.4 Device Functional Modes

7.4.1 ADC128S102-SEP Operation

Simplified schematics of the ADC128S102-SEP in both track and hold operation are provided in Figure 7-3 and Figure 7-4, respectively. In Figure 7-3, the ADC128S102-SEP is in track mode: switch SW1 connects the sampling capacitor to one of eight analog input channels through the multiplexer, and SW2 balances the comparator inputs. The ADC128S102-SEP is in this state for the first three SCLK cycles after \overline{CS} is brought low.

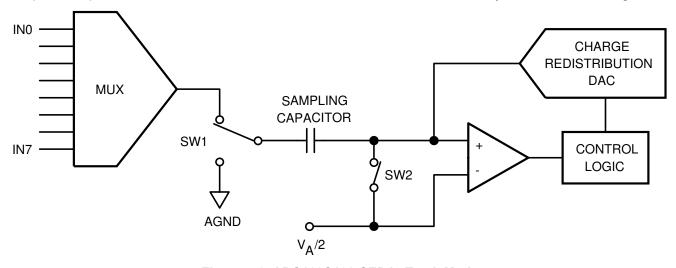


Figure 7-3. ADC128S102-SEP in Track Mode

Figure 7-4 shows the ADC128S102-SEP in hold mode: switch SW1 connects the sampling capacitor to ground, maintaining the sampled voltage, and switch SW2 unbalances the comparator. The control logic then instructs the charge-redistribution DAC to add or subtract fixed amounts of charge to or from the sampling capacitor until the comparator is balanced. When the comparator is balanced, the digital word supplied to the DAC is the digital representation of the analog input voltage. The ADC128S102-SEP is in this state for the last 13 SCLK cycles after $\overline{\text{CS}}$ is brought low.

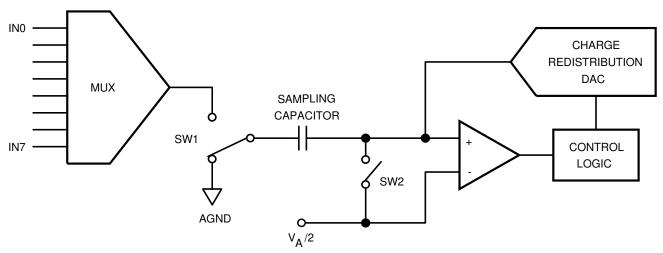


Figure 7-4. ADC128S102-SEP in Hold Mode

7.5 Programming

7.5.1 Serial Interface

An operational timing diagram and a serial interface timing diagram for the ADC128S102-SEP are illustrated in the *Timing Diagrams* section. \overline{CS} , chip select, initiates conversions and frames the serial data transfers. SCLK (serial clock) controls both the conversion process and the timing of serial data. DOUT is the serial data output pin, where a conversion result is sent as a serial data stream, MSB first. Data to be written to the control register are placed on DIN, the serial data input pin. New data are written to DIN with each conversion.

A serial frame is initiated on the falling edge of \overline{CS} and ends on the rising edge of \overline{CS} . Each frame must contain an integer multiple of 16 rising SCLK edges. The ADC DOUT pin is in a high-impedance state when \overline{CS} is high and is active when \overline{CS} is low. \overline{CS} is asynchronous and therefore functions as an output enable. Similarly, SCLK is internally gated off when \overline{CS} is brought high.

During the first three SCLK cycles, the ADC is in track mode, acquiring the input voltage. For the next 13 SCLK cycles the conversion is accomplished and the data are clocked out. SCLK falling edges 1 through 4 clock out leading zeros and falling edges 5 through 16 clock out the conversion result, MSB first. If there is more than one conversion in a frame (continuous conversion mode), the ADC re-enters track mode on the SCLK falling edge after the N \times 16th SCLK rising edge and re-enters the hold/convert mode on the N \times 16 + 4th SCLK falling edge. N is an integer value.

The ADC128S102-SEP enters track mode under three different conditions. In Figure 6-1, \overline{CS} goes low with SCLK high and the ADC enters track mode on the first SCLK falling edge. In the second condition, \overline{CS} goes low with SCLK low. Under this condition, the ADC automatically enters track mode and the \overline{CS} falling edge is taken as the first SCLK falling edge. In the third condition, \overline{CS} and SCLK go low simultaneously and the ADC enters track mode. Although there is no timing restriction with respect to the falling edges of \overline{CS} and SCLK, see Figure 6-3 for setup and hold time requirements for the \overline{CS} falling edge with respect to the SCLK rising edge.

www.ti.com

During each conversion, data are clocked into a control register through the DIN pin on the first eight SCLK rising edges after the fall of $\overline{\text{CS}}$. As given in Table 7-1, Table 7-2, and Table 7-3, the control register is loaded with data indicating the input channel to be converted on the subsequent conversion.

Although the ADC128S102-SEP can acquire the input signal to full resolution in the first conversion immediately following power up, the first conversion result after power up is that of a randomly selected channel. Therefore, incorporate a dummy conversion to set the required channel to be used on the subsequent conversion.

Table 7-1. Control Register Bits

BIT 7 (MSB)	BIT 6	BIT 5	BIT 4	BIT 3	BIT 2	BIT 1	BIT 0
DONTC	DONTC	ADD2	ADD1	ADD0	DONTC	DONTC	DONTC

Table 7-2. Control Register Bit Descriptions

BIT	SYMBOL	DESCRIPTION
7, 6, 2, 1, 0	DONTC	Don't care. The values of these bits do not affect the device.
5	ADD2	These three bits determine which input channel is sampled and converted at the next conversion cycle. The
4	ADD1	mapping between codes and channels is given in Table 7-3.
3	ADD0	

Table 7-3, Input Channel Selection

Ia	Table 7-3. Input Ghanner Selection											
ADD2	ADD1	ADD0	INPUT CHANNEL									
0	0	0	IN0									
0	0	1	IN1									
0	1	0	IN2									
0	1	1	IN3									
1	0	0	IN4									
1	0	1	IN5									
1	1	0	IN6									
1	1	1	IN7									

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The ADC128S102-SEP is a low-power, eight-channel, 12-bit ADC with specified performance specifications from 50 kSPS to 1 MSPS. The ADC128S102-SEP can be used at sample rates below 50 kSPS by powering the device down (deasserting \overline{CS}) in between conversions. The *Electrical Characteristics* table highlights the clock frequency where ADC performance is specified. There is no limitation on periods of time for shutdown between conversions.

8.2 Typical Application

Figure 8-1 shows a typical application block diagram. The split analog and digital supply pins are both powered in this example by the Texas Instruments' LP2950-N low-dropout voltage regulator. The analog supply is bypassed with a capacitor network located close to the ADC128S102-SEP. The digital supply is separated from the analog supply by an isolation resistor and bypassed with additional capacitors. The ADC128S102-SEP uses the analog supply (V_A) as its reference voltage; thus, V_A must be kept as clean as possible. Because of the low power requirements of the ADC128S102-SEP, a precision reference can also be used as a power supply.

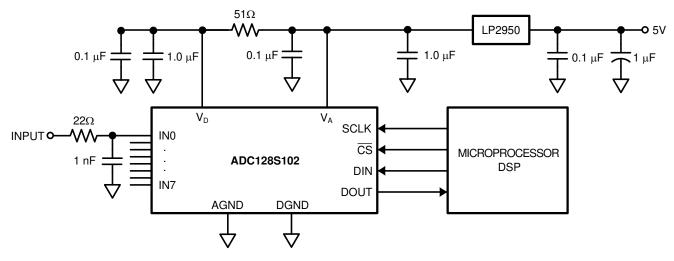


Figure 8-1. Typical Application Circuit

8.2.1 Design Requirements

A positive-supply-only data acquisition (DAQ) system is capable of digitizing up to eight single-ended input signals ranging from 0 V to 5 V with BW = 10 kHz and a throughput up to 500 kSPS. The ADC128S102-SEP must interface to an MCU whose supply is set at 5 V. To interface with an MCU that operates at 3.3 V or lower, V_A and V_D must be separated and care must be taken to ensure that V_A is powered before V_D .

Submit Document Feedback

Copyright © 2022 Texas Instruments Incorporated

8.2.2 Detailed Design Procedure

The signal range requirement forces the design to use a 5-V analog supply at V_A , the analog supply. This requirement stems from the fact that V_A is also a reference potential for the ADC. If the requirement of interfacing to the MCU changes to 3.3 V, the V_D supply voltage must also change to 3.3 V. The maximum sampling rate of the ADC128S102-SEP when all channels (eight) are enabled is $f_S = f_{SCLK} / (16 \times 8)$.

Faster sampling rates can be achieved when fewer channels are sampled. A single channel can be sampled at the maximum rate of f_S (single) = f_{SCLK} / 16.

The V_A and V_D pins are separated by a 51- Ω resistor to minimize digital noise from corrupting the analog reference input. If additional filtering is required, the resistor can be replaced by a ferrite bead, thus achieving a second-order filter response. Further noise consideration can be provided to the SPI interface, especially when the controller MCU is capable of producing fast rising edges on the digital bus signals. Inserting small resistances in the digital signal path can help reduce ground bounce, and thus improve overall noise performance of the system. Care must be taken when the signal source is capable of producing voltages beyond V_A . In such instances, the internal ESD diodes can start conducting. The ESD diodes are not intended as input signal clamps. To provide the desired clamping action, use Schottky diodes.

8.2.3 Application Curve

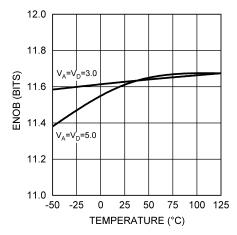


Figure 8-2. ENOB vs Temperature

9 Power Supply Recommendations

There are three major power supply concerns with this product: power-supply sequencing, power management, and the effect of digital supply noise on the analog supply.

9.1 Power-Supply Sequence

The ADC128S102-SEP is a dual-supply device. The two supply pins share ESD resources, so care must be exercised to ensure that power is applied in the correct sequence. To avoid turning on the ESD diodes, the digital supply (V_D) cannot exceed the analog supply (V_A) by more than 300 mV. Therefore, V_A must ramp up before or concurrently with V_D .

9.2 Power Management

The ADC128S102-SEP is fully powered up when \overline{CS} is low and is fully powered down when \overline{CS} is high, with one exception. If operating in continuous conversion mode, the ADC128S102-SEP automatically enters power-down mode between the 16th SCLK falling edge of a conversion and the 1st SCLK falling edge of the subsequent conversion (see Figure 6-1).

In continuous conversion mode, the ADC128S102-SEP can perform multiple conversions back to back. Each conversion requires 16 SCLK cycles and the ADC128S102-SEP performs conversions continuously as long as $\overline{\text{CS}}$ is held low. Continuous mode offers maximum throughput.

In burst mode, throughput can be traded off for power consumption by performing fewer conversions per unit time. In other words, more time is spent in power-down mode and less time is spent in normal mode. By using this technique, very low sample rates can be achieved while still using an SCLK frequency within the electrical specifications. To calculate the power consumption (P_C) , simply multiply the fraction of time spent in normal mode (t_N) by the normal mode power consumption (P_N) , as shown in Equation 1, and add the fraction of time spent in shutdown mode (t_S) multiplied by the shutdown mode power consumption (P_S) .

$$P_{C} = \frac{t_{N}}{t_{N} + t_{S}} \times P_{N} + \frac{t_{S}}{t_{N} + t_{S}} \times P_{S}$$
(1)

9.3 Power-Supply Noise Considerations

The charging of any output load capacitance requires current from the digital supply, V_D . The current pulses required from the supply to charge the output capacitance cause voltage variations on the digital supply. If these variations are large enough, they can degrade SNR and SINAD performance of the ADC. Furthermore, if the analog and digital supplies are tied directly together, the noise on the digital supply is coupled directly into the analog supply, causing greater performance degradation than noise alone causes on the digital supply. Similarly, discharging the output capacitance when the digital output goes from a logic high to a logic low dumps current into the die substrate, which is resistive. Load discharge currents cause *ground bounce* noise in the substrate that degrades noise performance if that current is large enough. The larger the output capacitance, the more current flows through the die substrate and the greater the noise coupled into the analog channel.

The first solution to keeping digital noise out of the analog supply is to decouple the analog and digital supplies from each other or use separate supplies for them. To keep noise out of the digital supply, keep the output load capacitance as small as practical. If the load capacitance is greater than 50 pF, use a $100-\Omega$ series resistor at the ADC output, located as close to the ADC output pin as practical. This resistor limits the charge and discharge current of the output capacitance and improves noise performance. Because the series resistor and the load capacitance form a low-frequency pole, verify signal integrity when the series resistor is added.

10 Layout

10.1 Layout Guidelines

Capacitive coupling between the noisy digital circuitry and the sensitive analog circuitry can lead to poor performance. The solution is to keep the analog circuitry separated from the digital circuitry and the clock line as short as possible.

Digital circuits create substantial supply and ground current transients. The logic noise generated can have significant impact upon system noise performance. To avoid performance degradation of the ADC128S102-SEP resulting from supply noise, do not use the same supply for the ADC128S102-SEP that is used for digital logic.

Generally, analog and digital lines cross each other at 90° to avoid crosstalk. However, to maximize accuracy in high-resolution systems, avoid crossing analog and digital lines altogether. Clock lines must be kept as short as possible and isolated from *all* other lines, including other digital lines. In addition, the clock line must be treated as a transmission line and be properly terminated.

Isolate the analog input from noisy signal traces to avoid coupling of spurious signals into the input. Any external component (for example, a filter capacitor) connected between the converter input pins and ground or to the reference input pin and ground must be connected to a very clean point in the ground plane.

Use a single, uniform ground plane and split power planes. The power planes must be located within the same board layer. Place all analog circuitry (input amplifiers, filters, reference components, and so forth) over the analog power plane. Place all digital circuitry and I/O lines over the digital power plane. Furthermore, all components in the reference circuitry and the input signal chain that are connected to ground must be connected together with short traces and enter the analog ground plane at a single, quiet point.

10.2 Layout Example

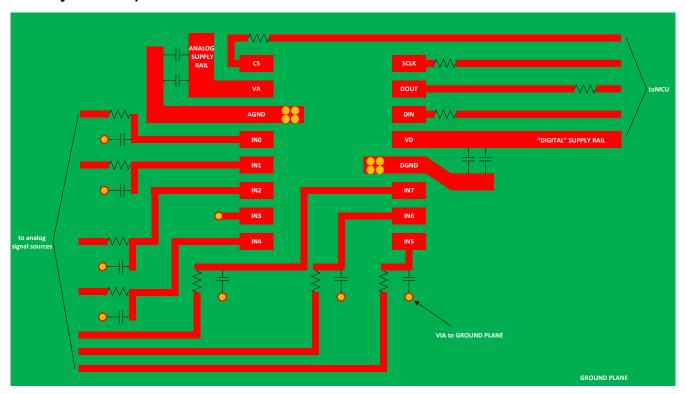


Figure 10-1. Layout Diagram



11 Device and Documentation Support

11.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

11.3 Trademarks

SPI[™] and QSPI[™] are trademarks of Motorola, Inc..

TI E2E[™] is a trademark of Texas Instruments.

MICROWIRE® is a registered trademark of Texas Instruments.

All trademarks are the property of their respective owners.

11.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

12.1 Engineering Samples

Engineering samples are available for order and are identified by *MPR* in the orderable device name (see *Packaging Information* at the end of this document). Engineering (MPR) samples meet the performance specifications of the data sheet at room temperature only and have not received the full space production flow or testing. Engineering samples may be QCI rejects that failed tests that do not impact the performance at room temperature, such as radiation or reliability testing.



www.ti.com 16-Mar-2023

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
ADC128S102PWTSEP	ACTIVE	TSSOP	PW	16	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	128S102	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 12-Dec-2023

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

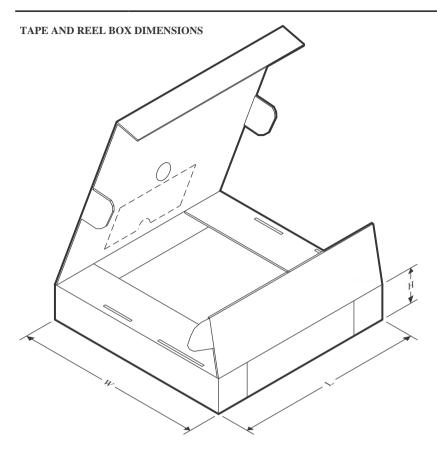
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

	Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
١	ADC128S102PWTSEP	TSSOP	PW	16	250	178.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

www.ti.com 12-Dec-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ADC128S102PWTSEP	TSSOP	PW	16	250	208.0	191.0	35.0



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2023, Texas Instruments Incorporated